UNIKC Semiconductor

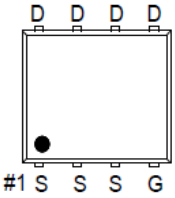
RoHS Compliant

PE537BA

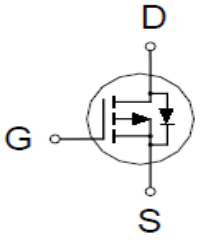
P-Channel Logic Level Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30V	9mΩ @V_{GS} = -10V	-33A



PDFN 3X3P



G : GATE
D : DRAIN
S : SOURCE

ABSOLUTE MAXIMUM RATINGS[4]

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current[3]	T_C = 25 °C	I_D	-33	A
	T_C = 100 °C		-20	
	T_A = 25 °C		-12	
	T_A= 70 °C		-9.3	
Pulsed Drain Current[1]		I_{DM}	-100	
Avalanche Current		I_{AS}	-34	
Avalanche Energy	L =0.1mH	E_{AS}	57.8	mJ
Power Dissipation	T_C = 25 °C	P_D	16.7	W
	T_C = 100 °C		6.7	
	T_A = 25 °C		2	
	T_A = 70 °C		1.3	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	$R_{\theta JA}$		60	°C / W
Junction-to-Case	$R_{\theta JC}$		7.5	

[1]Pulse width limited by maximum junction temperature.

[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C.

[3]Package limitation current is 22A.

[4]T_A = 25 °C Unless Otherwise Noted.

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ELECTRICAL CHARACTERISTICS[3]

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.6	-3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±25V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24V, V_{GS} = 0V			-1	μA
		V_{DS} = -20V, V_{GS} = 0V, T_J = 55 °C			-10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = -4.5V, I_D =-12A		9.9	16	mΩ
		V_{GS} = -10V , I_D = -12A		6.9	9	
Forward Transconductance[1]	g_{fs}	V_{DS} = -10V, I_D = -12A		35		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1MHz		2464		pF
Output Capacitance	C_{oss}			374		
Reverse Transfer Capacitance	C_{rss}			271		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		4		Ω
Total Gate Charge[2]	Q_g(V_{GS}= -10V)	V_{DS} = -15V ,I_D = -12A		56		nC
	Q_g(V_{GS}= -4.5V)			28		
Gate-Source Charge[2]	Q_{gs}			8		
Gate-Drain Charge[2]	Q_{gd}			12		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD}= -10V, I_D ≅ -12A, V_{GS} = -10V, R_{GEN}= 6Ω		21		nS
Rise Time[2]	t_r			25		
Turn-Off Delay Time[2]	$t_{d(off)}$			100		
Fall Time[2]	t_f			73		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Current	I_S				-12.8	A
Forward Voltage[1]	V_{SD}	I_F = -12A, V_{GS} = 0V			-1.3	V
Reverse Recovery Time	t_{rr}	I_F = -12A, dI/dt = 100A / μS		26		nS
Reverse Recovery Charge	Q_{rr}			14		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]T_J = 25 °C, Unless Otherwise Noted.

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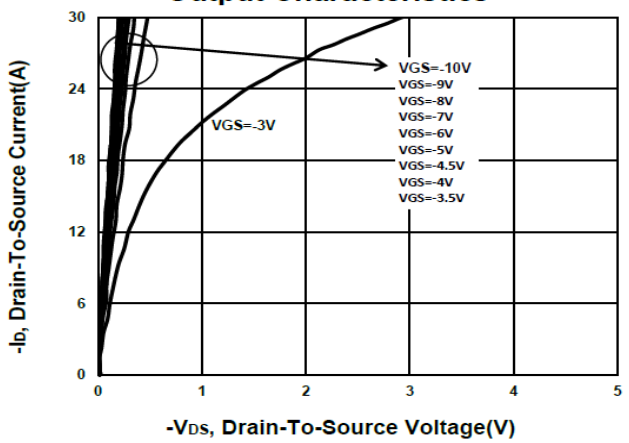
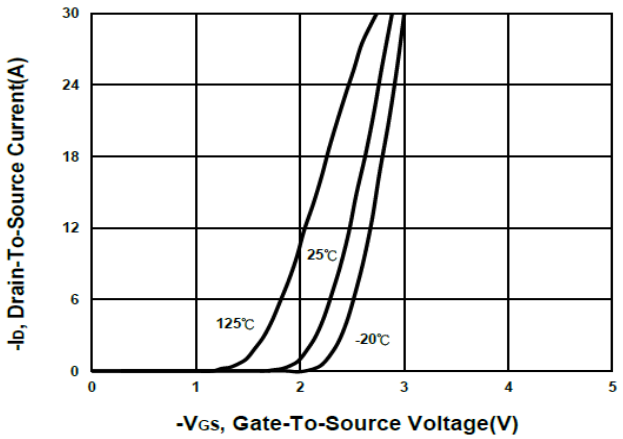
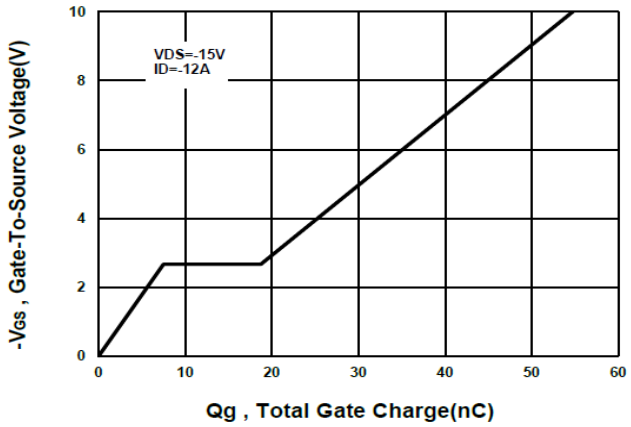
Output Characteristics



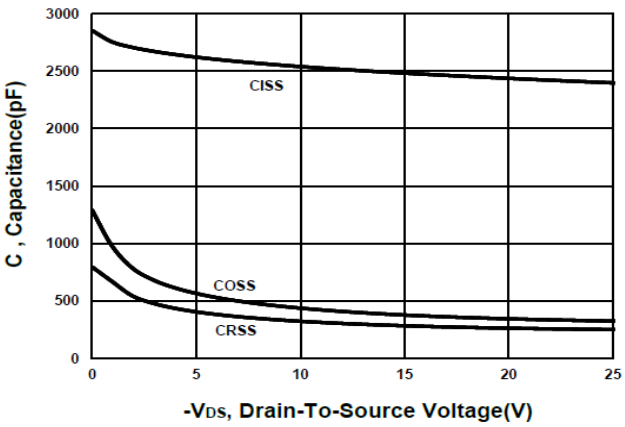
Transfer Characteristics



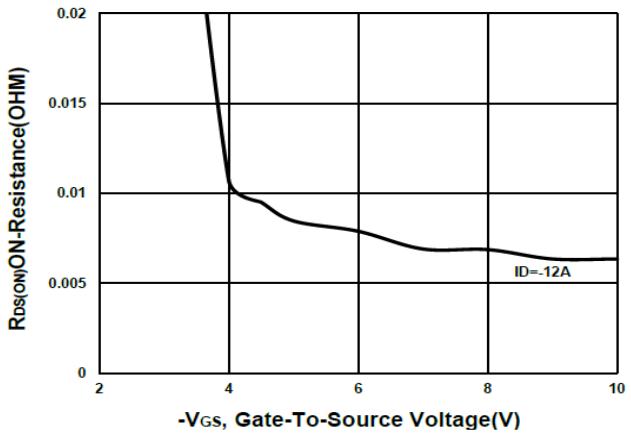
Gate charge Characteristics



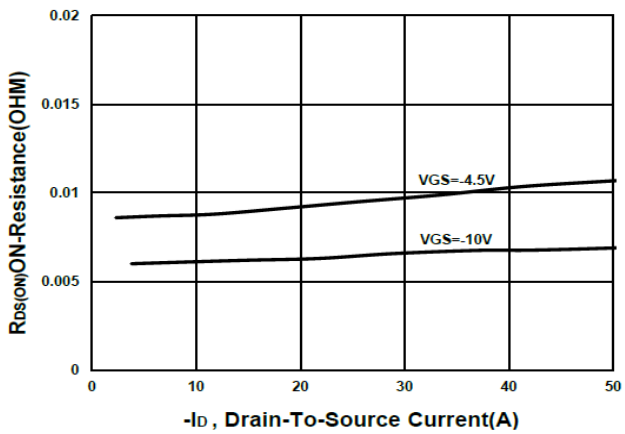
Capacitance Characteristic



On-Resistance VS Gate-To-Source



On-Resistance VS Drain Current



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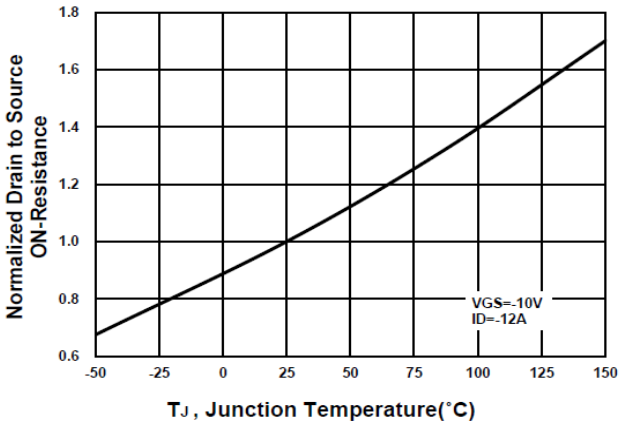
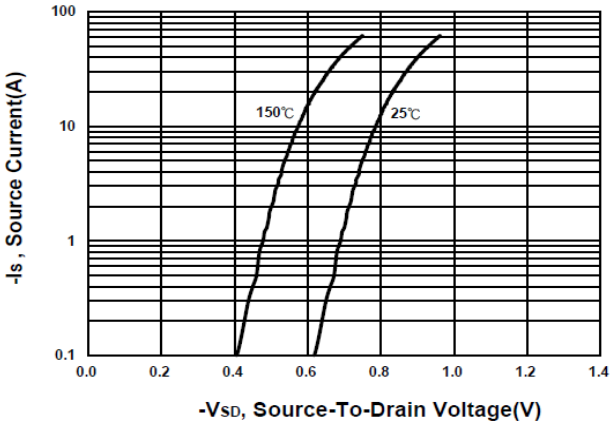
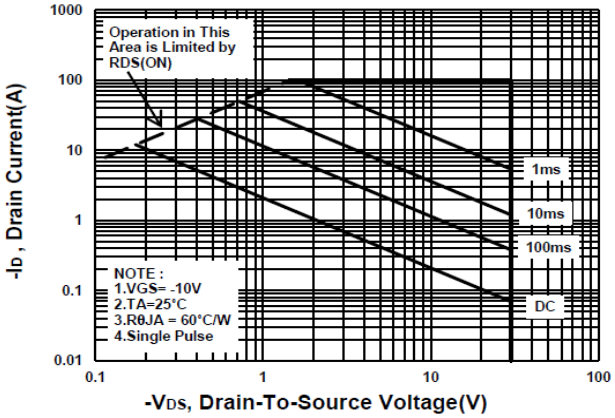
On-Resistance VS Temperature



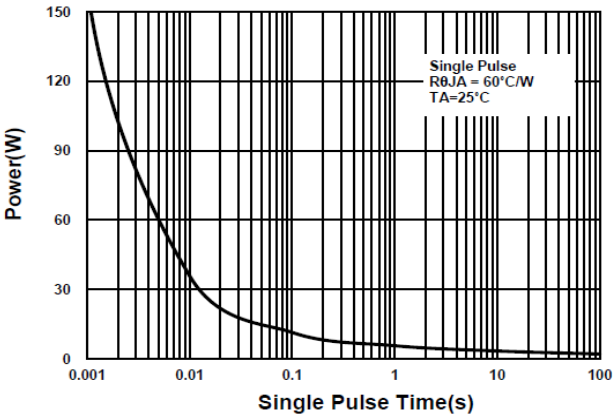
Source-Drain Diode Forward Voltage



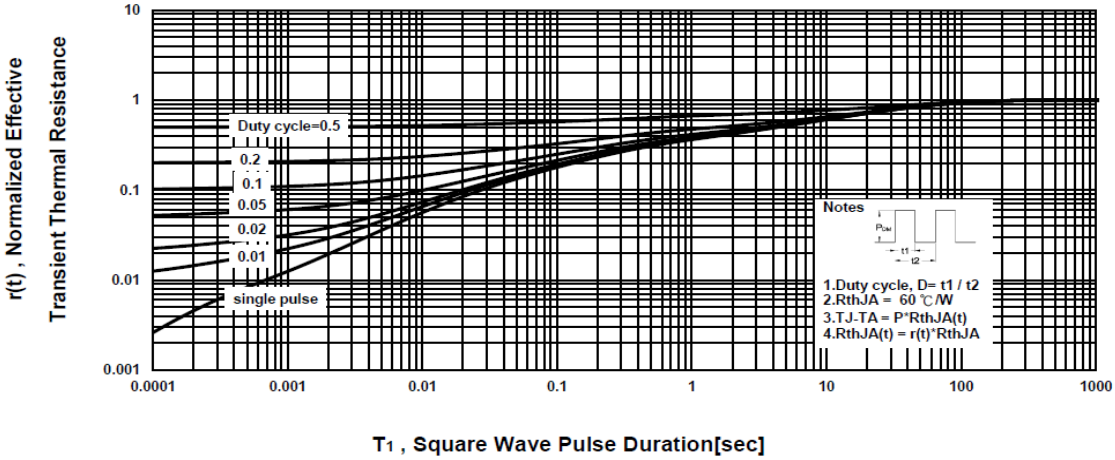
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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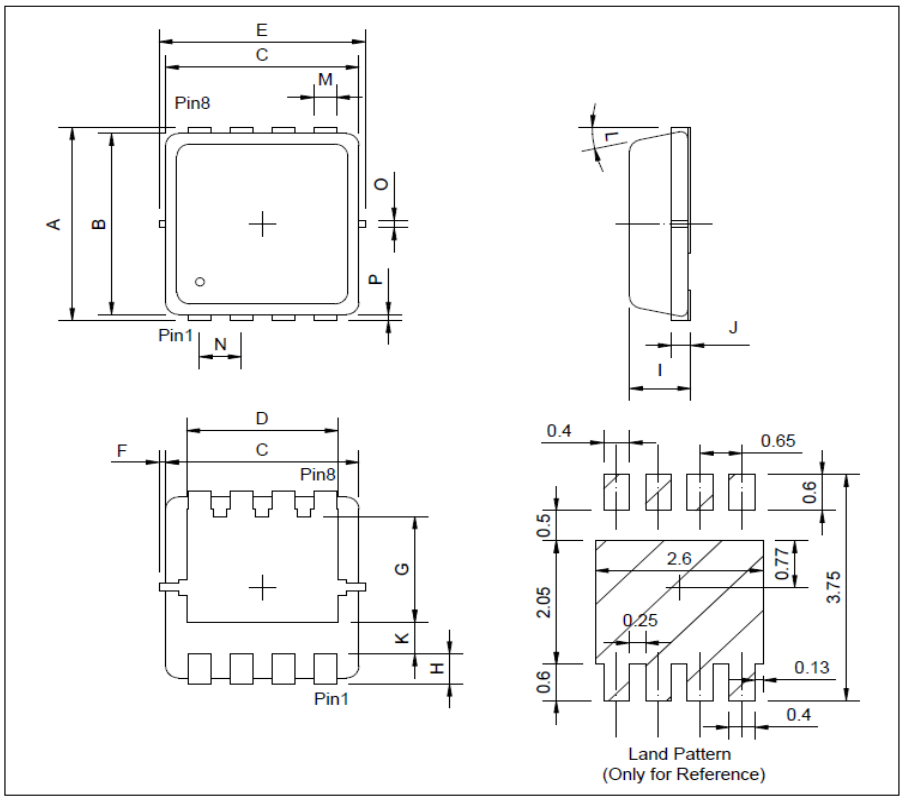
Package Dimension

PDFN 3x3P MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	3	3.3	3.6	I	0.65	0.8	0.9
B	2.88	3	3.2	J	0.1	0.15	0.25
C	2.9	3	3.25	K	0.59		
D	2.29	2.45	2.69	L	0°	10°	12°
E	3	3.3	3.6	M	0.14	0.3	0.4
F	0	0.1	0.2	N	0.55	0.65	0.75
G	1.35	1.75	2.2	O		0.2	
H	0.15	0.3	0.55	P	0		0.2



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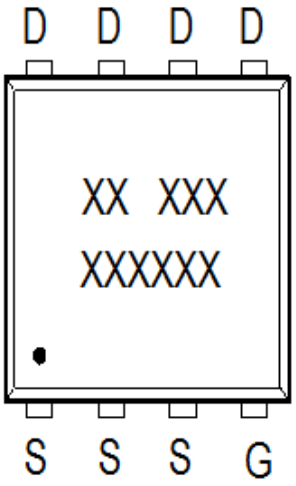
A. Marking Information(此产品代码为：J4）

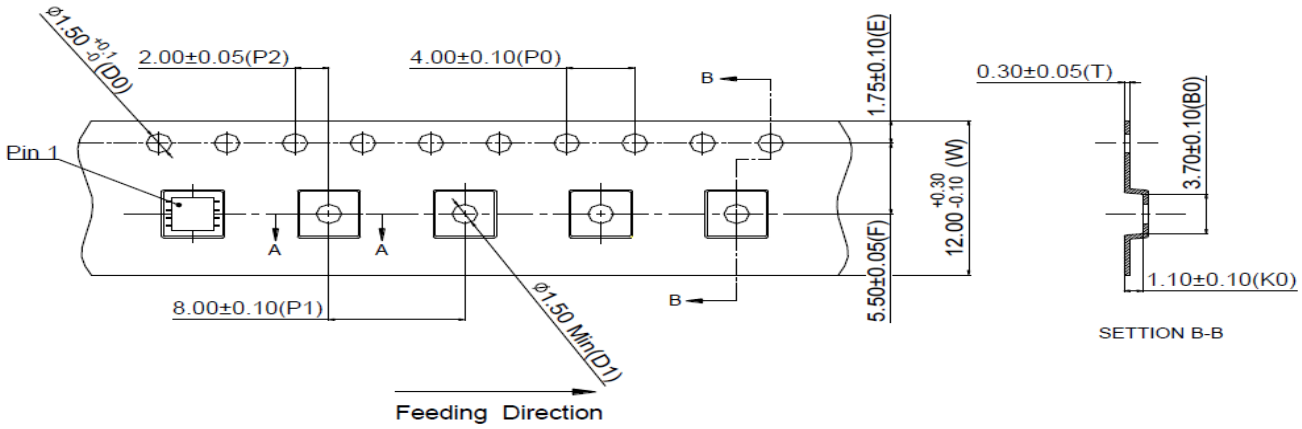


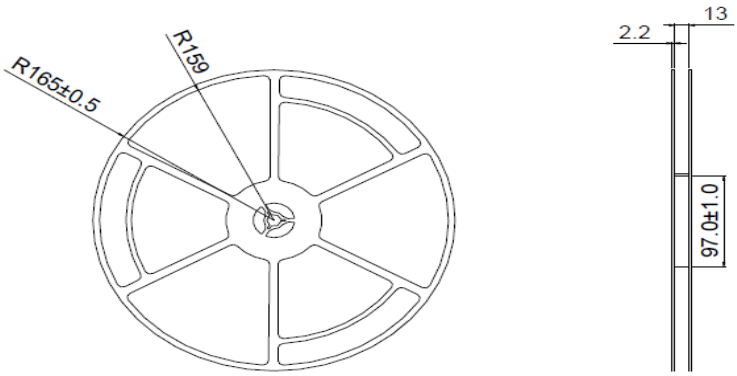
XX(前两码):产品代码

XXX

XXXXX(后九码):LOT NO

B. Tape&Reel Information:5000pcs/Reel





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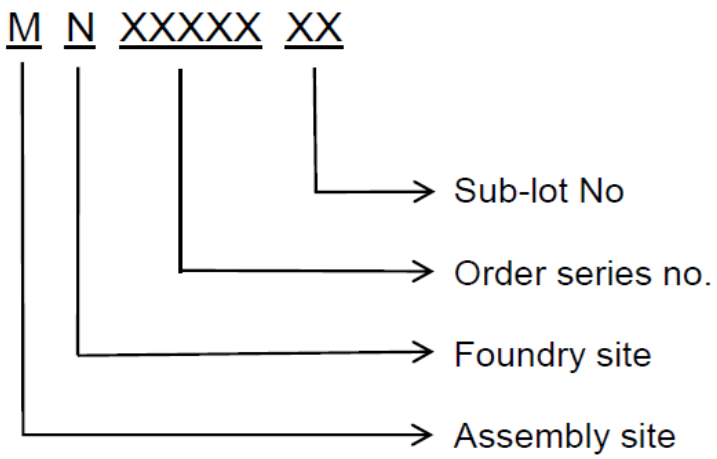
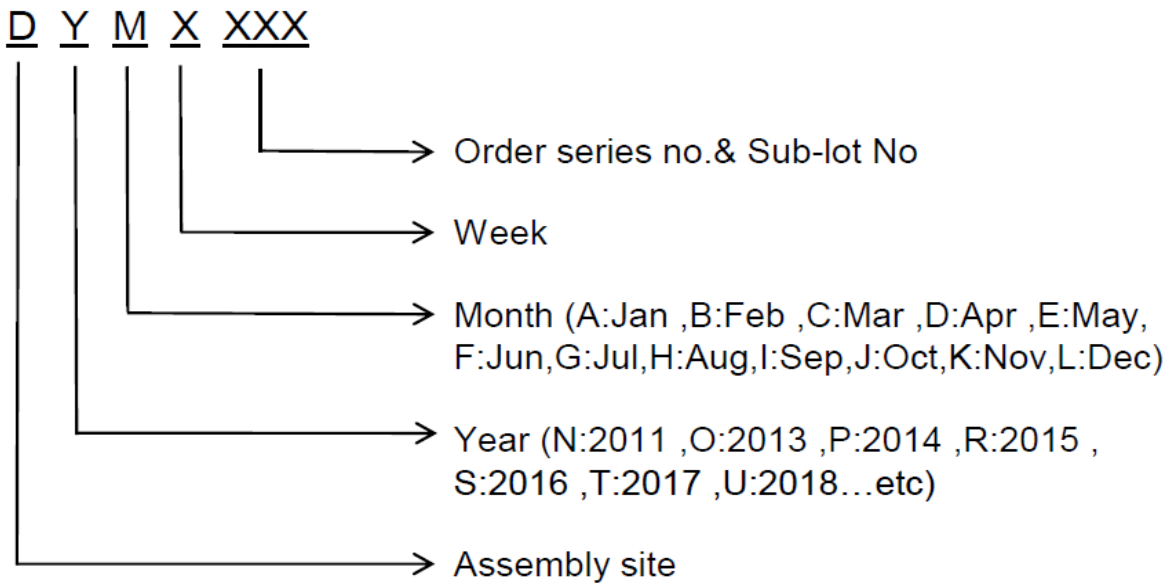
C. Lot No.&Date Code rule

1.Lot No.



2.Date Code



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D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文”0”和数字”0”，”G和”Q”的字型即可)
3	U-NIKC	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	RoHS label	RoHS long axis: 12 mm minor axis:6 mm bottom color: White Font color: Black Font style: Arial
11	Halogen Free label	G Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial
12	Scan information	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least